UCL Université catholique de Louvain Institute of Mechanics, Materials and Civil Engineering & Research Center on Architectured and Composite Materials (ARCOMAT) & Research center in micro and nanoscopic materials and electronic devices (CERMIN)

Damage and fracture in thin films and other nano-objects

T. Pardoen



Workshop "Lancement ERC TimeMan" Villeneuve-d'Ascq, 6 février 2019





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Fracture of thin films and coating dictates the reliability of a variety of modern technologies

Flexible electronics



Nomura, Kenji et al. Nature (2004) S. Coyle. MRS Bull (2007) Philips' fluid' smartphone

Thin functional coatings

on glass, steel, Al, etc ... must resist :

- thermomech. loadings
- forming operations after deposition
- impact
- scratch and wear





Mems and Nems



F. Iker, N. André, T. Pardoen, J.-P. Raskin, JMEMS (2006)

Micro and nano-electronics

Fracture due to ratcheting



Huano: Suo. Ma. JMPS 50, 1079 (2002)

"Mud cracking" in BCB



Lin & Vassak, unpublished (2003)





Delamination and fracture of dielectrics

Electromigration



Chinas & Clincke, JAP 88, 6302 (2000) He & Suo, JAP 85, 4639 (2004) Courtesy of J. Vlassak

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The analysis of the fracture of thin films allows unravelling fundamental elementary damage mechanisms – if possible in situ – direct interest for the preferate minerals of Patrick !









1. Introduction

2. Fracture of thin films on substrates

- test methods and extraction of *G*
- example 1 : CrN on polymer (indentation)
- example 2 : Au on polymer (for flexible electronics)

3. Fracture of freestanding films

- test methods for measuring the fracture strength & strain
- fracture strength of brittle films (case of PolySi)
- fracture strain of ductile films (case of AI)
- fracture toughness

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Approach 1 : Thin films on substrate

Nanoindentation

Tensile testing on elastomer









and many others: thermal loading, bending, etc

Basic expression of energy release rate for thin film (on substrate) fracture and delamination

Holding the plates at the loading grips fixed (du=0)



 $G = \frac{\partial W_{extForces}}{\partial A} - \frac{\partial W_e}{\partial A} = -\frac{\partial W_e}{\partial A}$

$$\Delta W_e = -Z \Big(\begin{smallmatrix} \alpha, \beta, \text{geometry} \\ \text{loadingpatern} \end{smallmatrix} \Big) \frac{\sigma^2}{2E} a^2 h$$
$$G = -\frac{\partial W_e}{\partial A} = -\frac{1}{h} \frac{\Delta W_e}{\Delta a} = Z \frac{\sigma^2}{E} a$$

$$\Delta W_e = -Z \left(\substack{\alpha, \beta, \text{geometry}, \\ \text{loadingpatern}} \right) \frac{\sigma^2}{2E} a h^2$$
$$G = -\frac{\partial W_e}{\partial A} = -\frac{1}{h} \frac{\Delta W_e}{\Delta a} = Z \frac{\sigma^2}{E} h$$

G independent of *a* for films on substrate

Z. Suo, in *Encyclopedia of Comprehensive Structural Integrity*, 2006

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$$G = Z \begin{pmatrix} \alpha, \beta, \sigma_{Y_s}, \text{ crack path, geometry} \\ \text{plasticity, viscoelasticity} \end{pmatrix} \frac{\sigma_R^2 h}{E_f}$$



General relationship for thin film (on substrate) fracture and delamination under tensile loading

 $G = Z(\alpha, \beta, \text{crack path, geometry}) \frac{\sigma_R^2 h}{\Gamma}$



Surface Crack Z = 3.951 Z here for no elastic mismatch and infinitely thick substrate (+ remember, G_c also depends on α and β through ψ)



Channeling

Z = 1.976



Substrate Damage

Z = 3.951





Spalling Z = 0.343

Debond $Z = \begin{cases}
1.028 \text{ (initiation)} \\
0.5 \text{ (steady - state)}
\end{cases}$

Hutchinson & Suo, Adv Appl Mech 1992



Example 1 : cracking resistance of CrN films on polymer

(as representative of many hard brittle coatings on softer substrates)

Thin Solid Films 550 (2014) 464-471



System of interest



Contents lists available at ScienceDirect

Thin Solid Films

journal homepage: www.elsevier.com/locate/tsf

Fracture toughness measurement of ultra-thin hard films deposited on a polymer interlayer

Audrey Favache ^{a,*}, Laure Libralesso ^b, Pascal J. Jacques ^a, Jean-Pierre Raskin ^c, Christian Bailly ^d, Bernard Nysten ^d, Thomas Pardoen ^a



Observation of channel cracks upon deposition





 $G = Z \begin{pmatrix} \alpha_{(polymer)}, \beta_{(polymer)}, \\ \text{channel crack spacing} \end{pmatrix} \frac{\sigma_R^2 h}{E_f}$ $\alpha = \frac{E_f^* - E_s^*}{E_f^* + E_s^*} \text{ and } \beta = \frac{\mu_f (1 - 2\nu_s) - \mu_s (1 - 2\nu_f)}{2\mu_f (1 - \nu_s) + 2\mu_s (1 - \nu_f)},$ weak effect for channel cracks if $\alpha > 0$ $\widehat{S_{u_f}^{\circ}} = 0$



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Observation of channel cracks upon deposition

 $G = Z(\alpha_{polymer}, \beta_{polymer}, channelcrack) \frac{\sigma_R^2 h}{E_f}$

Crack propagation energy release rate calculated from initial cracking. For cracked samples $G = G_{Ic}$ (in italic). The 95% confidence interval given in brackets is calculated from the error on the internal stress and on the substrate modulus.

Sample	α	Crack spacing S [µm]	Ζ	$Z \qquad G \left[J/m^2 \right]$	
CrN–steel CrN–Si CrN–P1–steel CrN–P1–Si CrN–P2–steel CrN–P3–steel CrN–P4–steel	0.01 0.14 0.95 0.95 0.99 0.97 0.98	Uncracked Uncracked 48 ± 10 60 ± 15 100 ± 20 67 ± 10 56 ± 10 18000	2.0 2.2 14 14 39 22 29 28	0.7 [0.6, 0.8] 0.8 [0.7, 0.9] 4.9 [4.4, 6.5] 4.9 [4.4, 6.5] 13.2 [11.8, 14.6] 7.4 [6.6, 8.6] 9.7 [8.5, 11.2] 0.7 [8.7, 10.8]	
CrN-PI-Si	0.98	18000	28	9.7 [8.7, 10.8]	

Note : polymer interlayer favours cracking !



Indentation based cracking (more complex than for bulk !)





Chen and Bull, TSF 2009

Lower bound $U_{1} = \int_{\delta_{f}}^{\delta_{A}} P_{\sigma} \left(\frac{x - \delta_{f}}{\delta_{A} - \delta_{f}}\right)^{m} dx + P_{cr}(\delta_{B} - \delta_{A}) \text{ and } U_{2} = \int_{\delta_{f}}^{\delta_{B}} P_{cr} \left(\frac{x - \delta_{f}}{\delta_{B} - \delta_{f}}\right)^{n} dx.$ $G = \Delta U / \Delta A$

Note : cracking observed only with polymer interlayer !

Indentation based cracking

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Sample	α	Crack spacing S [µm]	Ζ	<i>G</i> [J/m ²]	G (J/m ²) from indent
CrN-steel	0.01	Uncracked	2.0	0.7 [0.6, 0.8]	
CrN-Si	0.14	Uncracked	2.2	0.8 [0.7, 0.9]	
CrN-P1-steel	0.95	48 ± 10	14	4.9 [4.4, 6.5]	
CrN-P1-Si	0.95	60 ± 15	14	4.9 [4.4, 6.5]	11.8 ± 5.6
CrN-P2-steel	0.99	100 ± 20	39	13.2 [11.8, 14.6]	
CrN-P3-steel	0.97	67 ± 10	22	7.4 [6.6, 8.6]	7.1 ± 5.7
CrN-P4-steel	0.98	56 ± 10	29	9.7 [8.5, 11.2]	
CrN-PI-Si	0.98	18000	28	9.7 [8.7, 10.8]	14.7 ± 10



Example 2 : cracking resistance of Au films on polymer

(as representative of metal on polymer flexible electronics type devices)



Thin Au films are not ductile (fracture strain below 1 or 2 %)





First ductilization principle : wrinkling patterns

Basic concept



5 to 30% of prestretch5 nm of Cr adhesion layer100 nm gold evaporatedUpon release, wavelet morphology

e.g. Lacour et al. IEEE, 2002





High stretchability without loss of electrical conductivity under monotonous and cyclic loadings







Second ductilization principles : 2D in plane or 3D out of plane structures

2D Serpentine pattern



3D structure of mushrooms



Low Scale No adhesion

Time consuming process

Expensive technology

++ Very low resistivity + Contact and integration - Elasticity



Third ductilization principle : retard or multiply necking



From Suo's group Li et al., Mech Mater 2005 Li & Suo, IJSS 2006 This requires playing with materials characteristics, e.g. strain hardening capacity and rate dependency (see next section of freestanding films)



Third ductilization principle : retard or multiply necking



The delocalization process optimisation depends also on stiffness mismatch



Li & Suo, IJSS 2006



Fourth ductilization principle : favour non percolating crack path

Starting point – why longitudinal cracks ? Large tensile stresses build up in the film in the transverse direction due to the transverse extension upon unloading after deposition





Fourth ductilization principle : favour non percolating crack path

If pulling next in longitudinal direction, wrinkles flatten and, then, long transverse cracks develop (depending on film fracture strain and possible – delayed – necking) interrupting electrical conduction





Fourth ductilization principle : favour non percolating crack path

How to avoid long percolating cracks ? One example : tri-branched pre-cracks





Example 1 of combination of strategies : Stretchable helical gold conductor



APPLIED PHYSICS LETTERS 91, 141911 (2007)

Stretchable helical gold conductor on silicone rubber microwire

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M. Troosters Neurotech SA, Chemin du Cyclotron 6, 1348 Louvain-la-Neuve, Belgium

Befahy et al., APL 2007



Process

Ph. D. of S. Befahy at UCL, 2006





Details of Step 2 of process : oxygen RF cold plasma on prestrained wires

to avoid delamination improve adhesion of PDMS

- Challenges
 - Presence of free siloxanes
 - Low surface energy (21-22 mJ/m2)
- Solutions
 - Solvent extraction
 - Surface activation (oxidation)
 - Low pressure plasma
 - UV (atmospheric pressure)
 - Ozone (atmospheric pressure)



Link with lecture 1



Details of Step 2 of process : oxygen RF cold plasma on prestrained wires

- Challenges
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- Solutions
 - Solvent extraction
 - Surface activation (oxidation)
 - Low pressure plasma
 - UV (atmospheric pressure)
 - Ozone (atmospheric pressure)
 - Titanium or Chromium intermediate thin layer (~5nm)



Link with lecture 1



Details of Step 3 of process : deposition

- Metallization by Physical Vapor Deposition
- ~5nm of titanium
- ~100nm of platinum or gold







Good adhesion !

Peel Scotch test





Details of Step 3 of process : deposition

- 5nm Ti and 80nm Au
- · Half the surface is covered





Details of Step 4 of process : release



Ph. D. of S. Befahy at UCL, 2006



In real



Patent PCT/EP2007/053159



Performances of the wires



9mm long 20 full rotations 25% of stretch Two different diameters

- 800µm diameter more stretchable
- at least 30% stretchability
- a minimum in the evolution of the resistance
- No sharp increase in resistance

Befahy e*t al.*, APL 2007 Ph. D. of S. Befahy at UCL, 2006

Quantitative characterization of cracking pattern

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Befahy et al., APL 2007


Surface morphology

200 nm



Adhesion OK Non percolating cracks OK Wrinkles OK

Befahy et al., APL 2007



Example of combination of strategies

Idea : play with substrate roughness to randomize crack pattern



Roughness 3



Roughness 4

Lambricht, Pardoen, Yunus, Acta Mater 2013

Example of combination of strategies

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Example of combination of strategies





Approach 1 : Thin films on substrate Conclusion

Pro and cons

- Easy to manipulate at macro level
- Adapted to macro testing devices
- **Closer to a system property to explore extrinsic effects**
- Difficulties to deconvolute substrate effects to estimate e.g. hardness or fracture toughness
- **Difficult to extract stress level**
- **Careful with internal stress**



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Approach 2 : Mechanical testing of freestanding small scale objects

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UCLouvain method : Fabrication of an elementary on chip micro- or nano- test structure

Start with Si wafer



Top view



Cross section view



Fabrication steps

Deposition of sacrificial layer (e.g. SiO₂)

Sacrificial layer

Substrate



Top view

Cross section view

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Fabrication steps

Deposition of the actuator layer involving large internal tensile stress (e.g. Si_3N_4)

\leftarrow	Actuator	\rightarrow
	Sacrificial layer	
	Substrate	



Top view

Stoney method to measure σ^{internal}

Cross section view



Fabrication steps

First photolithography





Top view

Cross section view



Cross section view





Cross section view



Fabrication steps

Starting point of the tensile test





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Fabrication steps

Release of the structures

(e.g. *HF wet etching*)





- Critical : etching selectivity
- Actuator is wider and specimen is thus released first
- Strain rate is not controlled



Measurement of displacement





Simulations of the release process









Principle of the force measurement













U









Both actuator and sample length can be varied.

3





Both actuator and sample length can be varied.

3





















Determination of fracture strain

Last unbroken structure



Specimen material





Discrete stress - strain curve



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Nanomechanical lab on chip

1 wafer

- 2 weeks of processing
- ~ 10.000 test structures





Shear tests








Notched specimens





- and many others ... -











and many others...











Lab-on-chip platform – *Last generation (#8)*

Global top view of the last generation masks 3 inches wafer



4 equivalent areas

All the structures are repeated 4 times

4*22 TEM compatible sets on 1 wafer

Lab-on-chip platform – Last generation (#8)



Backside opening

window

Actuator

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> Platform 1, 2 and 3: uniaxial tensile testing for brittle and ductile materials oLarge PAD dedicated to measure the thickness oStructures to extract the mismatch strain and the Young's modulus

Platform 4: Shear and biaxial tensile testings

Platform 5: Structures to extract the mismatch strain, pillars, single and double clamped beams



Lab-on-chip platform – Last generation (#8)





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Example 1 : Fracture strength of PolySi

(PolySi is THE enabling structural material for MEMS devices)

Start with single crystal Si micro and nanowires

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Contents lists available at ScienceDirect

Engineering Fracture Mechanics

journal homepage: www.elsevier.com/locate/engfracmech

Size dependent fracture strength and cracking mechanisms in freestanding polycrystalline silicon films with nanoscale thickness



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transgranular fracture in 240nm thick film



intergranular fracture in 40nm thick film



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Why trans- versus inter-?

by ACOM-TEM

Thickness (nm)	HAGB (%)	CSLB (%)	Σ3 (%)	LAGB (%)
240	64.2	30.2	14.5	5.6
40	70.4	23.7	9.8	5.9



- Same distribution of GB character
- Similar crystallite size
- More twin lamellae in 240 nm thick
- GB grooves on both types of films





Why trans- versus inter-?



We believe (!) that the larger relative amplitude of GB grooving in the 40nm thick film is the reason for the transition to intergranular fracture

To go deeper on PolySi fracture, the advise is to consult the excellent studies performed at Sandia Laboratory

APPLIED PHYSICS REVIEWS 2, 021303 (2015)

APPLIED PHYSICS REVIEWS

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Fracture strength of micro- and nano-scale silicon components

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Example 2 : fracture strain of AI thin films



Example of AI films

Pure AI evaporated films 2 thicknesses = 205 and 373 nm, grain size ≈ 180 and 230 nm

AISi1% evaporated films thickness = 200 nm, grain size ≈ 200 nm





Example of AI films





Clear evidences of stable necking





Large post necking ductility







In some specimens, fracture strain near 30%





Relaxation tests on AISi 1%



True strain [-]

m ≈ 0.1 to 0.15 Even larger in pure AI (too fast to be measured) (as explained by thermally activated deformation mechanisms, involving grain growth)





Metallic films fracture and nanowires by damage at GB







Example 3 : fracture of ZrNi metallic glass films



Zr₆₅Ni₃₅ films

DC-magnetron sputtering

at Plateforme Technologique Amont (PTA), Grenoble







Composition control

(Electron Problem Micro Analysis, EPMA)

- No impurities
- Uniform composition along the substrate



Thickness control

(cross-section SEM + mechanical profilometer)

Linear growth rate ~ 1 nm/s

Thickness ranges from 200 to 900 nm





DC-magnetron sputtered with thickness between 200 and 900 nm



Amorphous structure (presence of diffuse halos)

No peak shift (Q_P) and same FWHM for different thicknesses → atomic structure independent of thickness

M. Ghidelli et al., J. Alloys Compd., 615, 348-351 (2014)



Uniaxial tension response of 360 nm-thick Zr₆₅Ni₃₅ film



Elastic behavior up to 4% with E ~ 70 GPa (OK Brillouin spectro) Large fracture strain up to 15% (decreasing with increasing length) Yield stress around 2900 MPa



Fracture strain decreases with increasing specimen free surface



TEM shows no evidence of shear bands Fracture surface involve flat regions and corrugations (dimples)







Confirmation of the high rate sensitivity measured by nanoindentation



Fracture of Zr₆₅Ni₃₅ TFMGs

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Method: crack propagation from substrate + SEM observation



Corrugation pattern formation for thickness ≥ 500 nm

Presence of a folded layer for all thicknesses



←

Film thickness

M. Ghidelli et al., Scripta Materialia, 89 (2014) 9



Fracture of Zr₆₅Ni₃₅ TFMGs



Fracture toughness estimated by

$$K_c = \sigma_y \sqrt{40w}$$

 K_c → Fracture toughness σ_y → Yield strength w → corrugation width

Xi et al., Phys. Rev. Lett. 94, 125510 (2005)

Corrugation width \uparrow when thickness \uparrow Corrugation size << bulk values ~ mm (Xi *et al.* PRL 2005) Fracture toughness (2 to 4 MPa m^{1/2} << bulk values (K_c ~ 50 MPa m^{1/2})



Fracture of Zr₆₅Ni₃₅ TFMGs

Finite element simulations of static crack @ 900 nm film




Fracture of Zr₆₅Ni₃₅ TFMGs



Plastic collapse for 300 and 400 nm-thick film → mirror-like surface

M. Ghidelli e*t al.*, Acta Materialia (2015)



Fracture of Zr₆₅Ni₃₅ TFMGs

Is it possible to avoid the *plastic collapse* for thicknesses < 500 nm? Add a cap layer



Compressive plastic zone shifting into the SiO₂ layer and no folded layer

M. Ghidelli e*t al.*, Acta Materialia (2015)



Ultra-tough metallic glasses

Metallic glasses are wonderful materials except for their brittleness





Can we learn from this discovery to make ductile-tough metallic glasses ?



Ph. D. thesis M. Ghidelli, 2015 INPG + UCL e.g. Ghidelli *et al.,* Acta Mater 2015



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How to characterize the fracture resistance of thin freestanding films?

Freestanding configurations - challenges

• Initial crack tip opening displacement must be smaller than the critical crack tip opening displacement for valid fracture mechanics test

$$\delta_c \approx \frac{G_c}{\sigma_0} \quad \text{for } G_c = 1 \text{J/m}^2 \& \sigma_0 = 5 \text{ GPa}, \delta_c \approx 0.2 \text{ nm}$$

for $G_c = 10 \text{J/m}^2 \& \sigma_0 = 0.2 \text{ GPa}, \delta_c \gtrsim 50 \text{ nm}$

- Transfer of films without damaging
- Clamping

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- Detecting cracking initiation and crack growth
- Measure extremely small loads
- Generate statistically representative data



Two methods with valid cracks



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> (1) pre-crack by nanoindentation, release, pull in tension with microdevice, determine cracking initiation



S. Jaddi et al. JMPS 2019

(2) notched specimen, internal stressed actuator, release, cracking and arrest, measure final crack length









$$F = \left(\frac{(1 - v_a)L_a}{\frac{L_a}{t_a W_a^*} + \frac{E_a}{E}} \frac{C^*\left(a, \frac{W_a}{W}, \frac{L}{W}\right)}{2}\right) \sigma_a^{int}$$



Theoretical analysis

With short crack length, the test structures ressemble Center Cracked Panels (CCP) or Single Edge Notched Tension (SENT)



Limit 1: $L \approx W \& L < W_a$



Theoretical analysis SENT and CCP panels

$$K = \frac{F}{W^* t} Y\left(\frac{a}{W}\right) \sqrt{\pi a}$$

with
$$G = \frac{F^2}{2t} \frac{\partial C}{\partial a}$$
 and $G = \frac{K^2}{E^*}$

$$K_{SENTapprox} = (1 - \nu_{a})\sigma_{a}^{int}\sqrt{L_{a}}\sqrt{\frac{L_{a}}{L}}\frac{1.12\sqrt{\pi \frac{a}{W^{*}}}\sqrt{\frac{W^{*}}{L}}}{\frac{L_{a}}{L}\frac{W}{W_{a}}\frac{t}{t_{a}} + \frac{E_{a}}{2E}\left(\alpha_{2}1.12^{2}\pi \left(\frac{a}{W^{*}}\right)^{2}\frac{W^{*}}{L} + \alpha_{3}\right)}$$

$$K_{CCPapprox} = \frac{(1 - \nu_a)\sigma_a^{int}\sqrt{L_a}}{\sqrt{\frac{L_a}{L}}} \frac{\sqrt{\frac{L_a}{W^*}}\sqrt{\frac{W^*}{L}}}{\frac{L_a}{L}\frac{W}{W_a}\frac{t}{t_a} + \frac{E_a}{2E}\left(\alpha_2\pi\left(\frac{a}{W^*}\right)^2\frac{W^*}{L} + \alpha_3\right)}$$



Theoretical analysis

With longer crack lengths, the test structures ressemble Double Cantilever Beam geometry (DCB)



Limit 3:Wa<W & L≈W



Theoretical analysis

with
$$G = \frac{F^2}{2t} \frac{\partial C}{\partial a}$$
 and $G = \frac{K^2}{E^*}$

$$K_{DCBasym} = 4\sqrt{\frac{6}{\alpha_2}} (1 - \nu_a) \sigma_a^{int} \sqrt{L_a} \frac{\frac{a \ L^2}{W W^2} \sqrt{\frac{L_a}{L}}}{4\frac{E_a \ a^3}{E \ W^3} + \frac{L^3 \ L_a \ t}{W^3 W_a^* t_a}}$$

$$K_{DCBsym} = 2\sqrt{\frac{6}{\alpha_2}} (1 - \nu_a)\sigma_a^{int}\sqrt{L_a} \frac{\frac{a \ L^2}{WW^2}\sqrt{\frac{L_a}{L}}}{4\frac{E_a \ a^3}{E \ W^3} + \frac{L^3 \ L_a \ t}{W^3W_a^* t_a}}$$

Finite element analysis

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Verification : *K_I* scales linearly with internal stress in actuator











Cracking process in practice

Possible subcritical crack growth: environmental, creep...





Experimental results





Experimental problems

Mode III



Underetching



Stiction



Kinking out





Experimental problems

No cracking



Out of plane



No attachment



Undesired fracture





SiN of 55 nm



SiN of 93 nm





SiN of 55 nm



SiN of 93 nm







SiN of 55 nm



SiN of 93 nm





						ALC: NOT THE REPORT OF THE	
Ref.	L_a^*	L	W	W_a^*	$t=t_a$	a_{c_arrest}	K _{Ic}
number	[µm]	[µm]	[µm]	[µm]	[nm]	[µm]	[MPa√m]
Ι	15±1	10 ± 1	50±2	11±0.2	55±1	25.5 ±0.2	1.2±0.1
Π	10±1	10 ± 1	30±2	11±0.2	55±1	19±0.2	1.4±0.2
III	10±0.3	8±0.1	50±1	9±0.1	55 ±1	14.5±0.7	1.8±0.1
IV	85±4	8.8 ± 1	48±3	10.25 ± 0.3	93±1	26.9±0.1	1.7±0.3
V	62.4 ± 4	8.8 ± 1	48.3±2	$10.05\pm\!0.3$	93±1	27±0.2	1.4±0.2
VI	75.5 ± 2	9.1±1	48.5±1	10.25 ± 0.1	93±1	27.7±0.1	1.5±0.2
VII	85.9±4	9±1	48.2±4	10.25 ± 0.3	93±1	28.2 ±0.1	1.6±0.3
VIII	53±5	8.6±1.5	48.5±3	10.6 ± 0.7	93±1	18±1	2.9±0.1
IX	50 ± 6	8.6 ± 1.5	48±3	10.5 ± 0.3	93±1	20±1.2	2.1±0.3
X	53.5±5	9.4±1	48±1	9.8±0.3	93 ±1	24.4±0.2	1.6±0.2
XI	46.1±1	9±1	44±1	9.5±0.4	93±1	23±0.2	1.5±0.2
XII	65.2 ± 7	9±1	35±1	9.6±0.5	93±1	16.5±0.3	3.4±0.4
XIII	54±2	9±1	37±2	9.55±0.3	93±1	17.2±0.4	2.9±0.3
XIV	52.7±4	9±1	42±2	10.3±0.3	93±1	20.7 ± 0.2	2.1±0.4
XV	62.5 ± 2	9±1	39.2±1	10.3±0.5	93±1	21±1.5	2.4±0.05
K_{Ic_mean} ~ 2 MPa \sqrt{m}							

 K_c of 1.82 \pm 0.03 MPa.m^{1/2}

Pierron Group (2016) ACS Appl. Mater. Interfaces

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Median= 2.7 MPa \sqrt{m} $R^2 = 92\%$ Mean=2.9 MPa \sqrt{m}



Application to 150 nm thick SiO₂





Approach 2 : Freestanding thin films Conclusion

Pro and cons

Generate true intrinsic properties (but ...) – no artifact from substrate

Allow in situ TEM testing

Testing is complex – MEMS types devices help

Points of attention

- Importance of the state of the surface (oxide, roughness, ...)
- Higher strength at small scale but also higher rate sensitivity
- Huge effect of imperfections : statistical treatment essential
- Fracture toughness often not valid except if sufficiently brittle



1. Introduction

2. Fracture of films on substrates

- test methods and extraction of G
- example 1 : CrN on polymer (indentation)
- example 2 : Au on polymer (for flexible electronics)

3. Fracture of freestanding films

- test methods for measuring the fracture strength & strain
- fracture strength of brittle films
- fracture strain of ductile films
- fracture toughness